

# Jiang Yin

## List of Publications by Year in descending order

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31  
papers

807  
citations

471509

17  
h-index

477307

29  
g-index

32  
all docs

32  
docs citations

32  
times ranked

1389  
citing authors

#	ARTICLE	IF	CITATIONS
1	High-Performance Pentacene-Based Field-Effect Transistor Memory Using the Electrets of Polymer Blends. <i>Advanced Electronic Materials</i> , 2022, 8, .	5.1	10
2	Enhancement of Memory Properties of Pentacene Field-Effect Transistor by the Reconstruction of an Inner Vertical Electric Field with an n-Type Semiconductor Interlayer. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 13452-13458.	8.0	12
3	Enhanced Performance of Organic Field-Effect Transistor Memory by Hole-Barrier Modulation with an n-Type Organic Buffer Layer between Pentacene and Polymer Electret. <i>Advanced Electronic Materials</i> , 2020, 6, 1901184.	5.1	14
4	The magnetism of 1T-MX <sub>2</sub> (M = Zr, Hf; X = S, Se) monolayers by hole doping. <i>RSC Advances</i> , 2019, 9, 13561-13566.	3.6	16
5	Piezoelectricity in two-dimensional covalent organic frameworks. <i>Journal of Applied Physics</i> , 2017, 121, 225112.	2.5	0
6	Encoding, training and retrieval in ferroelectric tunnel junctions. <i>Scientific Reports</i> , 2016, 6, 27022.	3.3	8
7	Strain tunable magnetism in SnX <sub>2</sub> (X = S, Se) monolayers by hole doping. <i>Scientific Reports</i> , 2016, 6, 39218.	3.3	36
8	Quantum spin Hall insulator phase in monolayer WTe <sub>2</sub> by uniaxial strain. <i>AIP Advances</i> , 2016, 6, .	1.3	31
9	Tunable electronic structures in MPX <sub>3</sub> (M = Zn, Cd; X = S, Se) monolayers by strain engineering. <i>RSC Advances</i> , 2016, 6, 89901-89906.	3.6	19
10	Synthesis of Pbl <sub>2</sub> nanowires for high sensitivity photodetectors. <i>RSC Advances</i> , 2016, 6, 59445-59449.	3.6	20
11	Carrier-tunable magnetism in two dimensional graphene-like C <sub>2</sub> N. <i>RSC Advances</i> , 2016, 6, 54027-54031.	3.6	28
12	Unexpected Magnetic Semiconductor Behavior in Zigzag Phosphorene Nanoribbons Driven by Half-Filled One Dimensional Band. <i>Scientific Reports</i> , 2015, 5, 8921.	3.3	88
13	The development of BiFeO <sub>3</sub> -based ceramics. <i>Science Bulletin</i> , 2014, 59, 5161-5169.	1.7	40
14	Continuously-tuned tunneling behaviors of ferroelectric tunnel junctions based on BaTiO <sub>3</sub> /La <sub>0.67</sub> Sr <sub>0.33</sub> MnO <sub>3</sub> heterostructure. <i>AIP Advances</i> , 2014, 4, .	1.3	7
15	Enhanced half-metallicity in the zigzag graphene nanoribbons by adsorption of the zigzag hydrogen fluoride molecular chains. <i>AIP Advances</i> , 2014, 4, 067132.	1.3	0
16	Enhanced leakage current properties of HfO <sub>2</sub> /GaN gate dielectric stack by introducing an ultrathin buffer layer. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 152-156.	2.2	3
17	Memristive learning and memory functions in polyvinyl alcohol polymer memristors. <i>AIP Advances</i> , 2014, 4, .	1.3	20
18	The roles of the dielectric constant and the relative level of conduction band of high-k composite with Si in improving the memory performance of charge-trapping memory devices. <i>AIP Advances</i> , 2014, 4, 117110.	1.3	4

#	ARTICLE	IF	CITATIONS
19	Structural Evolving Sequence and Porous $\text{Ba}_6\text{Zr}_2\text{Nb}_8\text{O}_{38}$ Ferroelectric Ceramics with Ultrahigh Breakdown Field and Zero Strain. <i>Journal of the American Ceramic Society</i> , 2013, 96, 555-560.	3.8	17
20	Crystallization, phase evolution and ferroelectric properties of sol-gel-synthesized $\text{Ba}_{0.8}\text{Zr}_{0.2}\text{O}_3$ - $\text{x}(\text{Ba}_{0.7}\text{Ca}_{0.3})\text{TiO}_3$ thin films. <i>Journal of Materials Chemistry C</i> , 2013, 1, 522-530.		97
21	Upward ferroelectric self-polarization induced by compressive epitaxial strain in (001) $\text{BaTiO}_3$ films. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	48
22	The interface inter-diffusion induced enhancement of the charge-trapping capability in $\text{HfO}_2/\text{Al}_2\text{O}_3$ multilayered memory devices. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	44
23	The effect of thermal treatment induced inter-diffusion at the interfaces on the charge trapping performance of $\text{HfO}_2/\text{Al}_2\text{O}_3$ nanolaminate-based memory devices. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	54
24	Electron-beam induced phase transformation in $\text{Ag}_2\text{Se}$ thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 135-138.	1.8	6
25	Enhanced memory performance by tailoring the microstructural evolution of $(\text{ZrO}_2)_{0.6}(\text{SiO}_2)_{0.4}$ charge trapping layer in the nanocrystallites-based charge trap flash memory cells. <i>Applied Physics A: Materials Science and Processing</i> , 2012, 108, 217-222.	2.3	15
26	Redox-controlled memristive switching in the junctions employing Ti reactive electrodes. <i>AIP Advances</i> , 2011, 1, 032141.	1.3	3
27	Preparation and characterization of $\text{GeTe}_4$ thin films as a candidate for phase change memory applications. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	13
28	Memristive behaviors of $\text{LiNbO}_3$ ferroelectric diodes. <i>Applied Physics Letters</i> , 2010, 97, 012902.	3.3	40
29	A $\text{TiAl}_2\text{O}_5$ nanocrystal charge trap memory device. <i>Applied Physics Letters</i> , 2010, 97, 143504.	3.3	37
30	$\text{Ga}_2\text{Te}_3$ phase change material for low-power phase change memory application. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	39
31	Conduction behavior change responsible for the resistive switching as investigated by complex impedance spectroscopy. <i>Applied Physics Letters</i> , 2007, 91, .	3.3	38